

20A 200V SchottkyBarrierDiode

1 Description

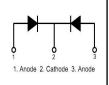
Dual center tab Schottky rectifier suited for High Frequency server and telecom base station SMPS. Packaged in TO Inside the package, this device combineshigh current rating and low volume to enhance both reliability and power density of the application.

2 Features

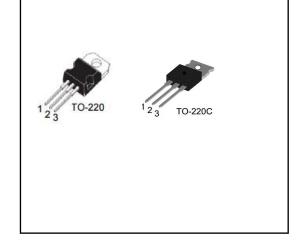
- High junction temperature capabiliy
- Low leakage current
- Low thermal resistance
- High frequency operation

3 Applications

- converters
- free-wheeling diodes
- reverse battery protection
- Typical applications are in switching power



 $V_{BR} = 200V$ $V_{F(single)(Max)} = 0.95V$ $I_{F(AV) (single)} = 10A$



4 Electrical Characteristics

4.1 Absolute Maximum Ratings (Tc=25 $^{\circ}$ C,unless otherwise noted)

PARAMETER		SYMBOL	VALUE	UNIT	
Peak Repetitive Reverse Voltage			V _{RRM}	200	V
RMS Reverse Voltage			V _{R(RMS)}	160	V
DC Blocking Voltage			V _R	200	V
Average Rectified Forward Current(single) TO-220F,Tc=90°C			10	Α	
Average Rectified Forward Current(double) TO-220/263/252/251,Tc=120°C		I _{F(AV)}	20	Α	
Repetitive Peak Surge Current(single)			I _{FRM}	15	А
Nonrepetitive Peak Surge Current(single) tp=8.3ms		I _{FSM}	150	Α	
Reverse Surge Current (Note 1)			I _{RSM}	4	Α
Operating Junction Temperature Range			Tj	-55~150	$^{\circ}\!\mathbb{C}$
Storage Temperature Range			T _{stg}	- 55∼150	$^{\circ}$ C
ESD (Machine Model=C)				>400	V
ESD (Human Body Model=3B)				>8000	V
ESD(Noncontact)				>15000	V

4.2 Thermal Characteristics

PARAMETER	SYMBOL	VALUE	UNIT
Thermal Resistance, Junction to Case-sink	R _{thJC}	2.8	°C/W



4.3 Electrical Characteristics

(Tc=25[°]C,unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Maximum Instantaneous	V _F	I _F =10A	-	0.87	0.95	V
Forward Voltage(Note 3)		I _F = 10A, T _C = 125℃	-	-	0.85	V
		I _F = 20A	-	0.95	1.20	V
Maximum Instantaneous	I _R	V _R = 200V	-	2	100	uA
Reverse (Note 2)		V _R = 200V, T _C = 125°C	-	-	15	mA
Total capacitance	C _{tot}	V _R =4V f=1MHz	-	90	-	pF
DC Blocking Voltage	V _{BR}	I _R =100uA	205	230	-	V

Notes:

- 1. 2.0us Pulse Width, f=1.0 KHz
- 2. Pulse Test: 300us Pulse Width, 1% Duty Cycle
- 3. VF Instantaneous forward voltage (pw = $300\mu s$, D = 2%).

5 Typical characteristics diagrams

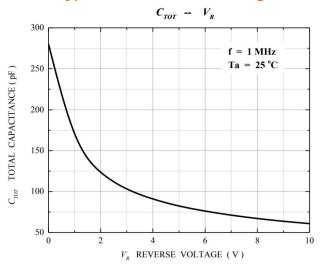


FIGURE 1. Total capacitance vs Voltage

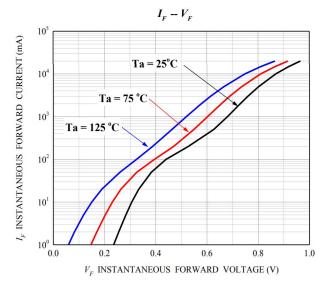


FIGURE 3. FORWARD CURRENT vs FORWARD VOLTAGE

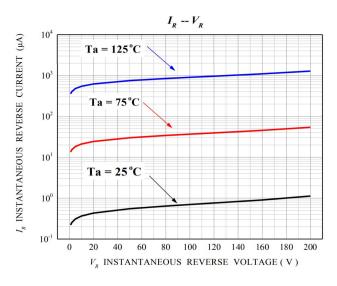


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

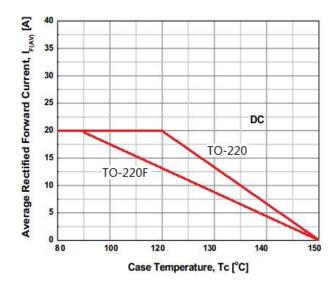


FIGURE 4. CURRENT DERATING CURVE

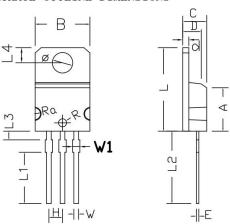


6 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
MBR20200CT	TO-220	MBR20200CT	Pb-free	Tube	1000/box

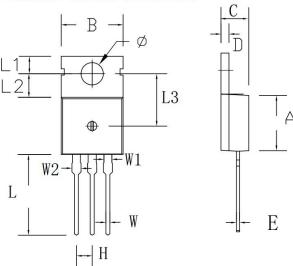
7 Dimensions

TO-220M PACKAGE OUTLINE DIMENSIONS



C1 - 1	Dimensions	In Millimeters	Dimensions	In Inches
Symbol	min.	max.	min.	max.
	MIN	MAX	MIN	MAX
A	7. 55	8.05	0. 297	0.317
В	9.85	10. 25	0. 388	0. 404
С	4. 20	4. 80	0. 165	0. 189
D	3. 20	3.60	0. 126	0. 142
Е	0.42	0.47	0.017	0.019
L	15. 20	15. 60	0. 598	0.614
Н	2. 52	2. 56	0.099	0. 101
W	0.78	0.88	0. 031	0. 035
Ф	3.60	3.90	0. 142	0. 154
R	0.72	0.78	0. 028	0. 031
Ra	9.00	10. 5	0. 354	0.413
d	1.10	1.40	0.043	0.055
L1	9.3	9.7	0. 366	0. 382
L2	13.00	13.60	0. 512	0. 535
L3	1. 20	1.70	0.047	0.067
L4	2.60	3. 0	0. 102	0.118
W1	1.10	1.50	0.043	0.059

TO-220C PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In	Millimeters	Dimensions	In Inches		
Symbol	min.	max.	min.	max.		
A	8. 80	9. 30	0. 346	0. 366		
В	9. 70	10.30	0.382	0.406		
С	4. 25	4. 75	0. 167	0. 187		
D	1. 20	1.45	0.047	0. 057		
Е	0. 40	0.60	0.016	0.024		
Н	2. 54	2. 54 TYP		0. 100 TYP		
W	0.60	0.95	0.024	0.037		
W1	1. 05	1.45	0.041	0.057		
W2	1. 20	1.60	0. 047	0.063		
L	12.60	13. 40	0. 496	0. 528		
L1	2. 45	2.95	0.096	0. 116		
L2	3. 45	3. 95	0. 136	0. 156		
L3	8. 15	8. 65	0. 321	0. 341		
Φ	3. 50	3. 90	0. 138	0. 154		



9 Attentions

- Jiangsu Donghai Semiconductor Co.,Ltd. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Jiangsu Donghai Semiconductor Co.,Ltd. products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

10 Appendix

Revision history:

Date	REV.	Description	Page
2018.09.20	1.0	Original	
2022.1.20	1.1	Modify company name	ALL